

MOS FIELD EFFECT TRANSISTOR μ PA2721GR

SWITCHING N-CHANNEL POWER MOSFET

DESCRIPTION

The µPA2721GR is N-channel MOS Field Effect Transistor designed for power management applications of notebook computers and Li-ion battery protection circuit.

FEATURES

· Low on-state resistance

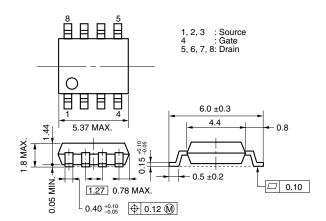
 $R_{DS(on)1} = 4.3 \text{ m}\Omega \text{ MAX.} \text{ (Vgs} = 10 \text{ V, I}_D = 10 \text{ A)}$ $R_{DS(on)2} = 6.3 \text{ m}\Omega \text{ MAX.}$ (Vgs = 4.5 V, ID = 10 A)

- Low Ciss: Ciss = 5100 pF TYP. (VDS = 10 V, VGS = 0 V)
- Built-in gate protection diode
- Small and surface mount package (Power SOP8)

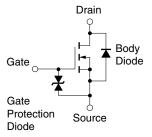
ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA2721GR-E1	Power SOP8
μPA2721GR-E1-A ^{Note}	Power SOP8
μ PA2721GR-E2	Power SOP8
μ PA2721GR-E2-A ^{Note}	Power SOP8

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



Note Pb-free (This product does not contain Pb in external electrode and other parts.)

ABSOLUTE MAXIMUM RATINGS (TA = 25°C, All terminals are connected.)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	30	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	V	
Drain Current (DC)	ID(DC)	±19	Α
Drain Current (pulse) Note1	ID(pulse)	±150	Α
Total Power Dissipation Note2	P _{T1}	1.1	W
Total Power Dissipation (PW = 10 sec) Note2	PT2	2.5	W
Channel Temperature	Tch	150	°C
Storage Temperature	T_{stg}	-55 to +150	°C

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

2. Mounted on glass epoxy board of 1 inch x 1 inch x 0.8 mm

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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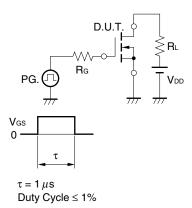


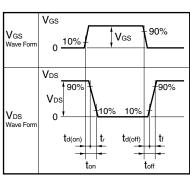
ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			1	μΑ
Gate Leakage Current	Igss	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.0		2.5	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10 V, I _D = 10 A	12			S
Drain to Source On-state Resistance Note	RDS(on)1	V _{GS} = 10 V, I _D = 10 A		3.4	4.3	mΩ
	RDS(on)2	V _{GS} = 4.5 V, I _D = 10 A		4.6	6.3	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		5100		pF
Output Capacitance	Coss	V _{GS} = 0 V		1050		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		690		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 10 A		23		ns
Rise Time	tr	V _{GS} = 10 V		40		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		113		ns
Fall Time	t _f			51		ns
Total Gate Charge	QG	V _{DD} = 15 V		51		nC
Gate to Source Charge	Qgs	V _{GS} = 5 V		13		nC
Gate to Drain Charge	Q _{GD}	I _D = 19 A		24		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 19 A, V _{GS} = 0 V		0.8		V
Reverse Recovery Time	trr	I _F = 19 A, V _{GS} = 0 V		48		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		52		nC

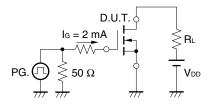
Note Pulsed

TEST CIRCUIT 1 SWITCHING TIME

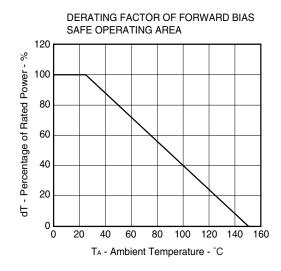


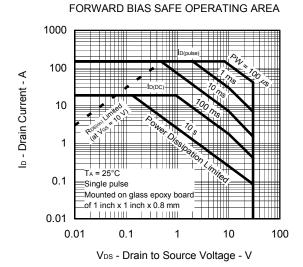


TEST CIRCUIT 2 GATE CHARGE

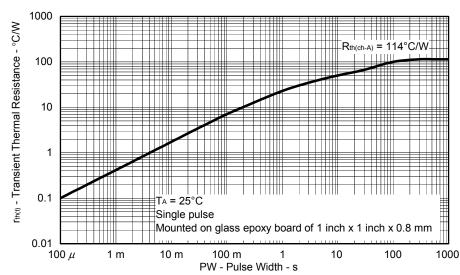


TYPICAL CHARACTERISTICS (TA = 25°C)

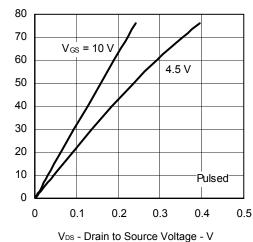




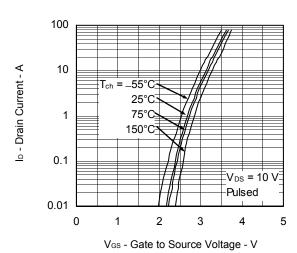
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH







FORWARD TRANSFER CHARACTERISTICS



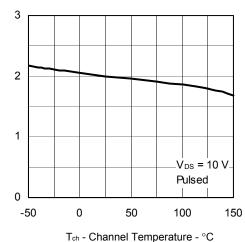
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lo - Drain Current - A

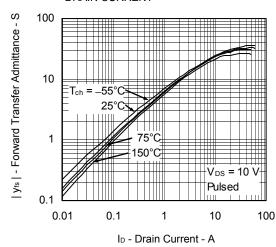
VGS(off) - Gate Cut-off Voltage - V

R_{DS(on)} - Drain to Source On-state Resistance - mΩ

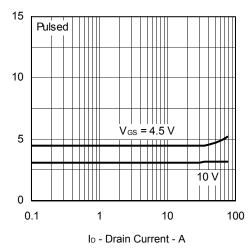
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



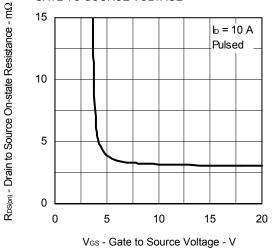
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



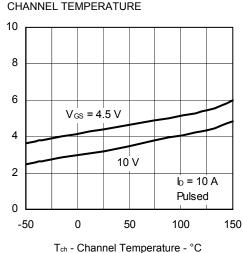
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



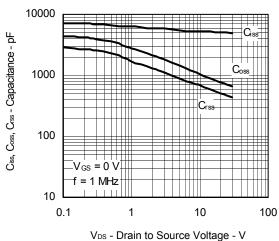
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



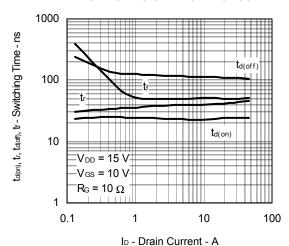
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



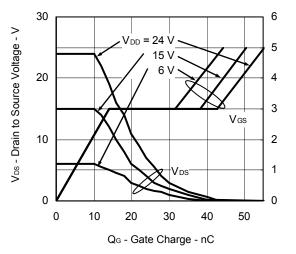
RDS(on) - Drain to Source On-state Resistance - m\Omega

Ves - Gate to Source Voltage - V

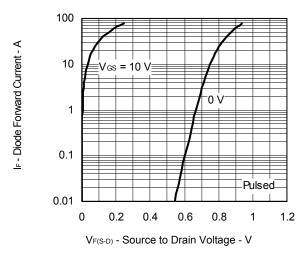
SWITCHING CHARACTERISTICS



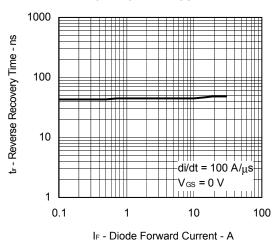
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT



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